

**Listing of Claims:**

Claim 1 (Currently Amended) A liquid crystal display device comprising:  
a substrate;  
a thin film transistor including a gate electrode, a source electrode, and a drain electrode on the substrate;  
a pixel electrode electrically connected to the drain electrode;  
a data line electrically connected with the source electrode;  
a first insulating layer, a pure amorphous silicon layer, and a doped amorphous silicon layer sequentially layered under the data line;  
a data pad at one end of the data line;  
a gate line electrically connected with the gate electrode; and  
a gate pad electrode at one end of the gate line,  
wherein the gate pad electrode is formed of a single layer directly on top of the first insulating layer, wherein the first insulating layer includes an opening that exposes a portion of the gate line, and  
wherein the gate pad electrode electrically contacts the exposed portion of the gate line and overlaps the first insulating layer,

Claim 2 (Original) The device of claim 1, wherein the pixel electrode is selected from a group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

Claim 3 (Currently Amended) A liquid crystal display device comprising:  
a substrate;  
a thin film transistor including a gate electrode, a source electrode, and a drain electrode  
on the substrate;

a pixel electrode electrically connected to the drain electrode;  
a data line electrically connected with the source electrode;  
a first insulating layer, a pure amorphous silicon layer, and a doped amorphous silicon  
layer sequentially layered under the data line;  
a data pad at one end of the data line;  
a gate line electrically connected with the gate electrode; and  
a gate pad electrode at one end of the gate line,  
wherein the gate pad electrode is formed directly on top of the first insulating layer,  
wherein the first insulating layer includes an opening that exposes a portion of the gate  
line,  
wherein the gate pad electrode electrically contacts the exposed portion of the gate line  
and overlaps the first insulating layer,  
~~The device of claim 1, wherein the drain electrode has a through hole that exposes a~~  
~~portion of the first insulating layer, and wherein the pixel electrode electrically contacts~~  
~~an inner side surface of the drain electrode via the through hole.~~

Claim 4 (Currently Amended) A liquid crystal display device comprising:

a substrate;  
a thin film transistor including a gate electrode, a source electrode, and a drain electrode  
on the substrate;  
a pixel electrode electrically connected to the drain electrode;  
a data line electrically connected with the source electrode;  
a first insulating layer, a pure amorphous silicon layer, and a doped amorphous silicon  
layer sequentially layered under the data line;  
a data pad at one end of the data line;  
a gate line electrically connected with the gate electrode;

a gate pad electrode at one end of the gate line; and

The device of claim 1, further including a data pad electrode, wherein the data pad has a data pad contact hole passing through the doped amorphous silicon layer and through the amorphous silicon layer, and wherein the data pad electrode electrically contacts an inner side surface of the data pad via the data pad contact hole[.],  
wherein the gate pad electrode is formed directly on top of the first insulating layer,  
wherein the first insulating layer includes an opening that exposes a portion of the gate line, and  
wherein the gate pad electrode electrically contacts the exposed portion of the gate line and overlaps the first insulating layer.

Claim 5 (Original) The device of claim 4, wherein said data pad electrode is comprised of the same material as said pixel electrode.

Claims 6-20 (Canceled)

Claim 21 (New) The device of claim 3, wherein the pixel electrode is selected from a group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

Claim 22 (New) The device of claim 4, wherein the pixel electrode is selected from a group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).